

Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>VS-MURB820TRLPBF</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



ISHAY www.vishay.com

Vishay Semiconductors

Ultrafast Rectifier, 8 A FRED Pt®



TO-263AB (D²PAK)





TO-262AA

FEATURES · Ultrafast recovery time



· Low forward voltage drop · Low leakage current

175 °C operating junction temperature

HALOGEN FREE

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

AEC-Q101 qualified

• Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Base cathode 0^2 N/C



VS-MURB820PbF

VS-MURB820-1PbF

PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	8 A
V_{R}	200 V
V _F at I _F	0.895 V
t _{rr}	35 ns
T _J max.	175 °C
Diode variation	Single die

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Peak repetitive reverse voltage	V_{RRM}		200	V				
Average rectified forward current	I _{F(AV)}	Total device, rated V _R , T _C = 150 °C	8					
Non-repetitive peak surge current	I _{FSM}		100	Α				
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16					
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER SYMBOL TEST		TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	200	-	-		
Forward voltage	V _F	I _F = 8 A	-	-	0.975	V	
Forward voitage		I _F = 8 A, T _J = 150 °C	-	-	0.895		
Dovorno logicado gurrent	I_	$V_R = V_R$ rated	-	-	5		
Reverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μΑ	
Junction capacitance	C _T	V _R = 200 V	-	25	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

Revision: 10-Jul-15 Document Number: 94081



Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VS-MURB820PbF, VS-MURB820-1PbF

www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS		TYP.	MAX.	UNITS		
		$I_F = 1.0 A, dI_F/dt =$	50 A/μs, V _R = 30 V	-	-	35			
Davaga wasayan dimas	t _{rr}	I _F = 0.5 A, I _R = 1.0 A, I _{REC} = 0.25 A		-	-	25	İ		
Reverse recovery time		T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs V _R = 160 V	-	20	-	ns A nC		
		T _J = 125 °C		-	34	-			
Dools was assent assument	I _{RRM}	T _J = 25 °C		-	1.7	-			
Peak recovery current		T _J = 125 °C		-	4.2	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	23	-			
		T _J = 125 °C		-	75	-			

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	3.0		
Thermal resistance, junction to ambient	R _{thJA}		-	-	- 50 °		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-		
\\/aimht			-	2.0	-	g	
Weight			-	0.07	-	OZ.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Maddanalanda		Case style TO-263AB (D2PAK)		MUF	RB820		
Marking device		Case style TO-262AA		MURI	B820-1		



VS-MURB820PbF, VS-MURB820-1PbF

www.vishay.com

Vishay Semiconductors

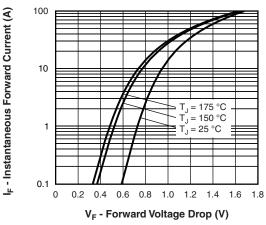


Fig. 1 - Typical Forward Voltage Drop Characteristics

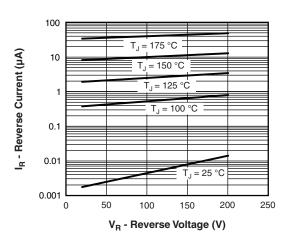


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

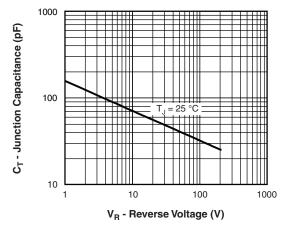


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

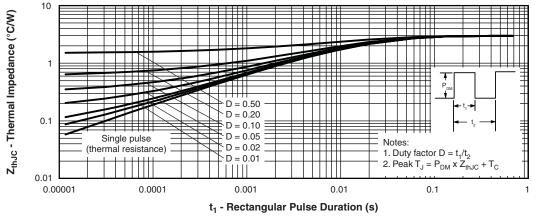


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

VS-MURB820PbF, VS-MURB820-1PbF

Vishay Semiconductors

VISHAY.

180

170

160

150

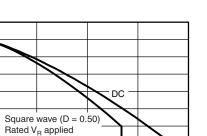
140

130

See note (1)

Allowable Case Temperature (°C)

www.vishay.com



I_{F(AV)} - Average Forward Current (A)

12

Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

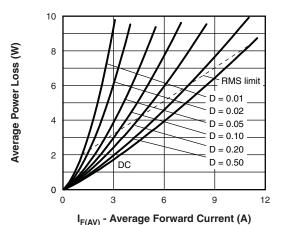


Fig. 6 - Forward Power Loss Characteristics

V_R = 160 V T_J = 125 °C T_J = 25 °C V_R = 160 V T_J = 16 A I_F = 8 A I_F = 4 A

Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

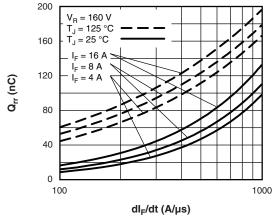


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: $T_C = T_J$ - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = $I_{F(AV)}$ x V_{FM} at ($I_{F(AV)}$ /D) (see fig. 6); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R

Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

VS-MURB820PbF, VS-MURB820-1PbF

VISHAY www.vishay.com

Vishay Semiconductors

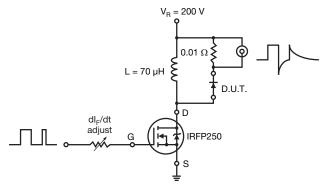
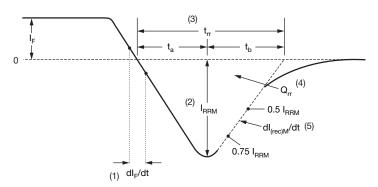


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_E/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



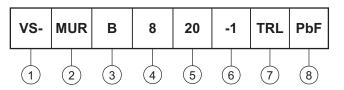


VS-MURB820PbF, VS-MURB820-1PbF

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Ultrafast MUR series

3 $B = D^2PAK/TO-262$

Current rating (8 = 8 A)

Voltage rating (20 = 200 V)

• None = D²PAK

• -1 = TO-262

7 • None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D2PAK package)

8 PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?95014</u>							
Part marking information	www.vishay.com/doc?95008						
Packaging information	www.vishay.com/doc?95032						

Revision: 10-Jul-15 Document Number: 94081



Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

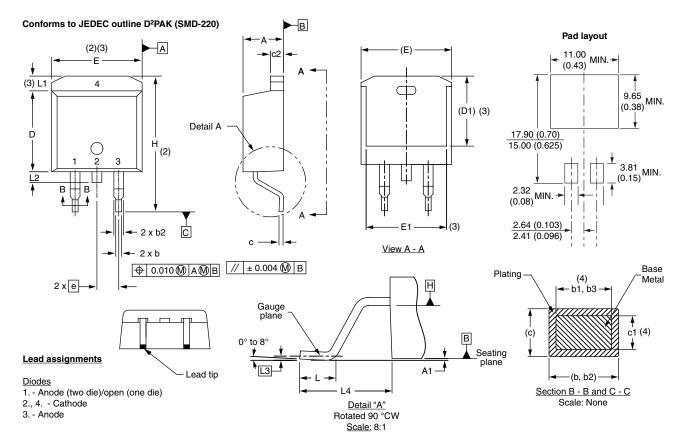


Outline Dimensions

Vishay High Power Products

D²PAK, **TO-262**

DIMENSIONS FOR D²PAK in millimeters and inches



SYMBOL MILLI	MILLIM	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	31MBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

Document Number: 95014 Revision: 31-Mar-09

For technical questions concerning discrete products, contact: diodes-tech@vishay.com For technical questions concerning module products, contact: ind-modules@vishay.com

Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

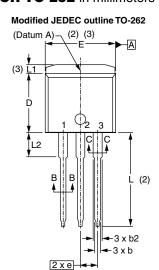
Outline Dimensions

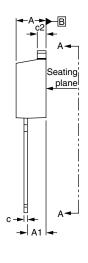
Vishay High Power Products

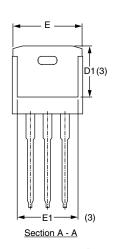
D²PAK, TO-262



DIMENSIONS FOR TO-262 in millimeters and inches







⊕ 0.010 A **M** B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

Section B - B and C - C
Scale: None

b1, b3

metal

CVMDOL	MILLIM	ETERS	INC	NOTEO	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-MURB820TRLPBF - DIODE GEN PURP 200V 8A D2PAK

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



Www.vishay.com

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000